

I<sub>C</sub>=500mA, I<sub>B</sub>=50mA

I<sub>C</sub>=1.0A, I<sub>B</sub>=200mA

 $V_{CE}$ =2.0V I<sub>C</sub>=250mA

V<sub>CF</sub>=2.0V, I<sub>C</sub>=250mA

 $V_{CE}$ =1.5V, I<sub>C</sub>=0.2A, f=1.0kHz

V<sub>CB</sub>=20V, I<sub>E</sub>=0, f=1.0MHz

 $V_{\mbox{\scriptsize CE}}\mbox{=}10\mbox{V}, \mbox{I}_{\mbox{\scriptsize C}}\mbox{=}10\mbox{MHz}$ 

V<sub>CE</sub>=2.0V, I<sub>C</sub>=1.0A

V<sub>CE(SAT)</sub>

V<sub>CE(SAT)</sub>

V<sub>BE(ON)</sub>

hFE

 $h_{FE}$ 

h<sub>fe</sub>

f<sub>T</sub> C<sub>ob</sub>



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## DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5679, 2N5681 series devices are complementary silicon power transistors, manufactured by the epitaxial planar process, designed for general purpose amplifier and switching applications where high voltages are required.

1.0

2.0

1.0

150

50

40

5.0

40

30

## MARKING: FULL PART NUMBER

MAXIMUM R	ATINGS: (T <sub>A</sub> =25°C unless otherwise	e noted) SYMBOL	2N5679 2N5681	2N5680 <u>2N5682</u>	UNITS		
Collector-Base Voltage		V <sub>CBO</sub>	100	120	V		
Collector-Emitter Voltage		VCEO	100	120	V		
Emitter-Base Voltage		VEBO	4	4.0			
Continuous Collector Current		IC	1	1.0			
Continuous Base Current		Ι <sub>Β</sub>	0	0.5			
Power Dissipation		PD	1	1.0			
Power Dissipation (T <sub>C</sub> =25°C)		PD	1	10			
Operating and Storage Junction Temperature		TJ, T <sub>stg</sub>	-65 to	-65 to +200			
Thermal Resistance		$\Theta_{JA}$	1	75	°C/W		
Thermal Resistance		$\Theta^{JC}$	17	7.5	°C/W		
ELECTRICAL CHARACTERISTICS: (T <sub>A</sub> =25°C unless otherwise noted)							
SYMBOL TEST CONDITIONS			MIN	MAX	UNITS		
I <sub>CBO</sub>	V <sub>CB</sub> =Rated V <sub>CBO</sub>			1.0	μA		
ICEV	V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>EB</sub> =1.5V			1.0			
I <sub>CEV</sub> V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>EB</sub> =1.5V, T <sub>C</sub> =150°C			1.0	mA			
ICEO	V <sub>CE</sub> =70V (2N5679, 2N5681)			10	μA		
ICEO	V <sub>CE</sub> =80V (2N5680, 2N5682)			10	μA		
I <sub>EBO</sub>	V <sub>EB</sub> =4.0V			1.0	μA		
BVCEO	I <sub>C</sub> =10mA (2N5679, 2N5681)		100		V		
BVCEO	I <sub>C</sub> =10mA (2N5680, 2N5682)		120		V		
V <sub>CE(SAT)</sub>	I <sub>C</sub> =250mA, I <sub>B</sub> =25mA			0.6	V		

R2 (2-December 2013)

V

V

V

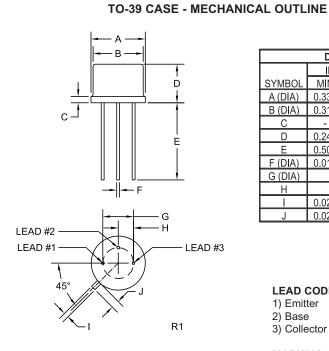
MHz

pF



2N5679 2N5680 PNP 2N5681 2N5682 NPN

COMPLEMENTARY SILICON POWER TRANSISTORS



DIMENSIONS								
	INCHES		MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
A (DIA)	0.335	0.370	8.51	9.40				
B (DIA)	0.315	0.335	8.00	8.51				
С	-	0.040	-	1.02				
D	0.240	0.260	6.10	6.60				
Е	0.500	-	12.70	-				
F (DIA)	0.016	0.021	0.41	0.53				
G (DIA)	0.200		5.08					
Н	0.100		2.54					
	0.028	0.034	0.71	0.86				
J	0.029	0.045	0.74	1.14				
TO-39 (REV: R1)								

LEAD CODE:

1) Emitter

2) Base 3) Collector

MARKING: FULL PART NUMBER

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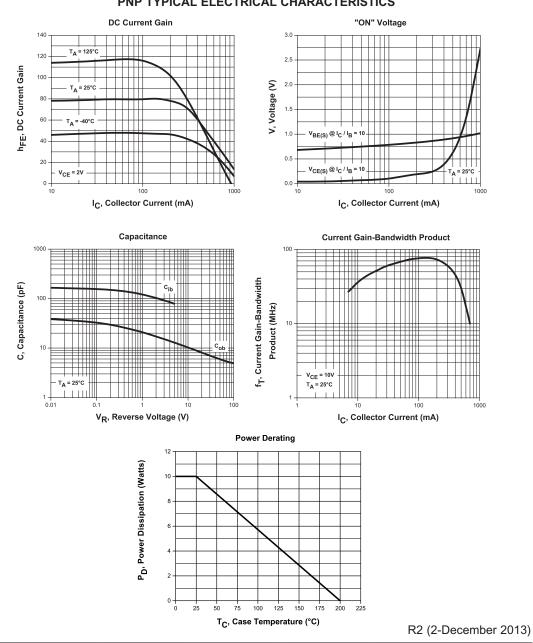
R2 (2-December 2013)



2N5679 2N5680 2N5681 2N5682 NPN COMPLEMENTARY

SILICON POWER TRANSISTORS

**PNP** 



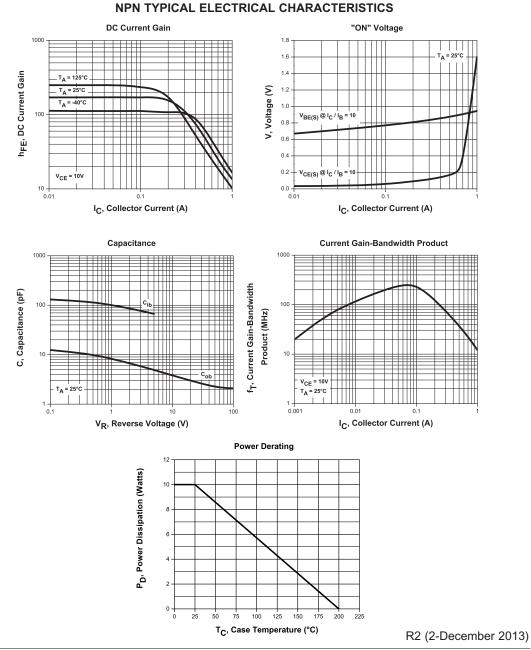
PNP TYPICAL ELECTRICAL CHARACTERISTICS

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**PNP** 2N5679 2N5680 2N5681 2N5682 NPN

COMPLEMENTARY SILICON POWER TRANSISTORS



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#### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

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- Inventory bonding
- Consolidated shipping options

#### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
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- Custom electrical curves
- · Environmental regulation compliance
- Customer specific screening
- · Up-screening capabilities

· Custom product packing

Custom bar coding for shipments

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

## REQUESTING PRODUCT PLATING

- If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when 1. ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

## CONTACT US

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